

# TRANSISTOR(PNP)

## FEATURES

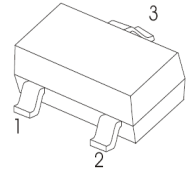
- Driver Transistors

**MARKING:2H**

## MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-4	V
I <sub>C</sub>	Collector Current	-500	mA
P <sub>C</sub>	Collector Power Dissipation	225	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	556	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

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1. BASE
2. EMITTER
3. COLLECTOR

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-4			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V, I <sub>E</sub> =0			-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-60V, I <sub>B</sub> =0			-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	100			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	100			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA			-0.25	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA			-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA, f=100MHz	50			MHz